L Number	Hits		DB	Time stamp
_	9844	((diaphragm membrane elastic\$5 flexible	USPAT;	2004/04/15 10:15
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$4)).clm.	EPO; JPO;	
			DERWENT; IBM TDB	
	10015	((diaphragm membrane elastic\$5 flexible	USPAT;	2002/10/01 07:54
	10013	deformable elastom\$5 resilient\$5) near2	US-PGPUB;	2002, 20, 02 0 10
		(conduct\$45)).clm.	EPO; JPO;	
			DERWENT;	Į.
			IBM_TDB	
-	7329		USPAT;	2002/10/01 07:57
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$45)).clm.	EPO; JPO; DERWENT;	
			IBM TDB	
_	10011	((diaphragm membrane elastic\$5 flexible	USPAT;	2002/10/01 07:57
	10011	deformable elastom\$5 resilient\$5) near2	US-PGPUB;	2002/10/01 0/10/
		(conduct\$5)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	733		USPAT;	2002/10/01 07:57
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$5)).clm.) and capacit\$5.clm.	EPO; JPO;	
			DERWENT;	
_	264	((((diaphragm membrane elastic\$5 flexible	IBM_TDB USPAT;	2002/10/01 07:57
-	204	deformable elastom\$5 resilient\$5) near2	US-PGPUB;	2002/10/01 07:37
		(conduct\$5)).clm.) and capacit\$5.clm.) and	EPO; JPO;	
		electrode.clm.	DERWENT;	
			IBM TDB	
-	53	((((diaphragm membrane elastic\$5 flexible	USPĀT;	2003/06/26 18:36
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	
		(conduct\$5)).clm.) and capacit\$5.clm.) and	EPO; JPO;	
		electrode.clm.) and (concentration	DERWENT;	
	17	impurity purity)	IBM_TDB	2003/06/26 18:28
-	17	<pre>(((((diaphragm membrane elastic\$5 flexible deformable elastom\$5 resilient\$5) near2</pre>	USPAT; US-PGPUB;	2003/06/26 18:28
		(conduct\$5)).clm.) and capacit\$5.clm.) and	EPO; JPO;	
		electrode.clm.) and (concentration	DERWENT;	
		impurity purity).clm.	IBM TDB	
_	700		USPAT;	2003/06/26 18:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	0.0	(/216/2) 2010) and imposited	IBM_TDB	2002/06/26 10:27
_	92	((216/2).CCLS.) and impurit\$4	USPAT; US-PGPUB;	2003/06/26 18:37
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	(((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:39
		concentration) and etch near1 pit	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	•	////216/2\ COIS \ and immunit\(\)	IBM_TDB USPAT;	2003/06/26 18:39
-	1	(((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch near1 pit) and	USPAT; US-PGPUB;	2003/06/26 18:39
		diaphragm	EPO; JPO;	
		araphragm	DERWENT;	
			IBM TDB	
_	23	((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:41
		concentration	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/04/55
-	20	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	USPĀT;	2003/06/26 18:48
		concentration) and etch	US-PGPUB;	
]			EPO; JPO; DERWENT;	
			IBM TDB	
	L	<u></u>	TDE TOB	<u> </u>

			T	
-	15	((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:32
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable elastom\$5 resilient\$5)	EPO; JPO; DERWENT;	
		elastom\$5 resilienc\$5)	IBM TDB	
_ `	3	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:26
~		concentration and etch and (diaphragm	US-PGPUB;	2003/00/20 19:20
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and etch near3	DERWENT;	
		(pit hole groove dip)	IBM TDB	
_	3	(((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:49
		concentration) and etch near3 (pit hole	US-PGPUB;	
		groove dip)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:57
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and electrode	DERWENT;	
		near3 dielectric near3 (film layer support	IBM_TDB	
		substrate cover\$4)	IICDATE.	2003/06/26 18:55
1 -	1	((((((216/2).CCLS.) and impurit\$4 near3 concentration) and etch) and (diaphragm	USPAT; US-PGPUB;	2003/00/20 18:35
	}	membrane elastic\$5 flexible deformable	EPO; JPO;	
1		elastom\$5 resilient\$5)) and electrode	DERWENT;	
		near3 dielectric near3 (film layer support	IBM TDB	
		substrate cover\$4)) and pressure		
_	1	(((((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 18:55
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and electrode	DERWENT;	
		near3 dielectric near3 (film layer support	IBM_TDB	
		substrate cover\$4)) and pressure) and		
		silicon		0000/06/06 10 04
=	11	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:04
		concentration) and etch) and (diaphragm membrane elastic\$5 flexible deformable	US-PGPUB; EPO; JPO;	
		elastom\$5 resilient\$5)) and pressure	DERWENT;	
		elastomas lesillentas), and plessure	IBM TDB	
_	6	(((((216/2).CCLS.) and impurit\$4 near3	USPAT;	2003/06/26 19:27
		concentration) and etch) and (diaphragm	US-PGPUB;	
		membrane elastic\$5 flexible deformable	EPO; JPO;	
		elastom\$5 resilient\$5)) and pressure near3	DERWENT;	
	1	(sens\$4 measur\$3 detect test transducer	IBM_TDB	
		gauge monitor evaluate estimat\$4 identif\$4		
		indicat\$4)		0000/06/06 50 55
-	44167	impurit\$4 near3 concentration	USPAT;	2003/06/26 19:27
	1		US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	1092	(impurit\$4 near3 concentration) and	USPAT;	2003/06/26 19:29
	1092	pressure near3 (sens\$4 measur\$3 detect	US-PGPUB;	
		test transducer gauge monitor evaluate	EPO; JPO;	
		estimat\$4 identif\$4 indicat\$4)	DERWENT;	
			IBM_TDB	
-	18	((impurit\$4 near3 concentration) and	USPAT;	2003/06/26 19:30
		pressure near3 (sens\$4 measur\$3 detect	US-PGPUB;	
		test transducer gauge monitor evaluate	EPO; JPO;	1
		estimat\$4 identif\$4 indicat\$4)) and etch	DERWENT;	
1		near3 (pit groove hole dip)	IBM_TDB	0000 /00 /00 00 55
-	13	(((impurit\$4 near3 concentration) and	USPAT;	2003/06/26 19:32
		pressure near3 (sens\$4 measur\$3 detect	US-PGPUB;	
		test transducer gauge monitor evaluate estimat\$4 identif\$4 indicat\$4)) and etch	EPO; JPO; DERWENT;	
		near3 (pit groove hole dip)) and	IBM TDB	
		(diaphragm membrane elastic\$5 flexible		
		deformable elastom\$5 resilient\$5)		
		<u> </u>		1

2004/04/15 10:51 deformable elasticates resilient(5) near 2							
Conduct\$4 same etch\$4 same density	-	29	(diaphragm membrane elastic\$5 flexible		2004/04/15	10:51]
Comparison membrane elastic\$5 flexible deformable elastom\$5 resilient\$3) near2 conduct\$4 same etch\$4 same pit same density	1						
1	ı		conduct\$4 same etch\$4 same density				
disphragm membrane elastic\$5 flexible USFAT; Conduct\$4 same etch\$4 same pit same Conduct\$4 same etch\$4 same Conduct\$4 same Conduct\$5 sa	ı			1			
deformable elastom\$5 resilient\$5) near2	ı	, ,	(diambraco mombrano olastic\$5 flovible		2004/04/15	10.22	
Conduct\$4 same etch\$4 same pit same EPO; JPO; DERWENT; IBM TOB USPAT; US-COPUB;	_	3			2004/04/13	10.23	
DERWENT; IBM TDB USPAT;	ı				j		l
IBM TDB US-FGPUB EPO; JPO; DERWENT; IBM TDB US-FAT; US-FGPUB EPO; JPO; DERWENT; US-FGPUB EPO; JPO; DERWENT; US-FGP	į						
Company			density				
- 1 ((361/283.1-283.4).CCLS.) and etch\$4 same pit same density	_	658	(361/283.1-283.4).CCLS.		2004/04/15	10:24	
- 1 ((361/283.1-283.4).CCLS.) and etch\$4 same pit same density - 0 ((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$3) same density - 0 ((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$3) same density - 0 ((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$4) SPFRT; US-PGPUB; EFO, JPO; DERWENT; IBM TDB USPRT; US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPRT; US-PG			(000,000)	·			1
1 ((361/283.1-283.4).CCLS.) and etch94 same IBM TDB USPAT; USP-CPUB; EPC; JPC; DERWENT; EPC; JPC; DERWENT; E				EPO; JPO;			
1 ((361/283.1-283.4).CCLS.) and etch\$4 same pit same density - 0 ((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$\$) same density - 0 ((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$\$) same density - 0 ((361/283.1-283.4).CCLS.) and etch\$4 near3 (pit\$4 hole\$4 groove\$4 recess\$4 opening\$\$4\$) same density - 919 ((361/283.1-283.4).CCLS.) and 73/754.ccls.							
Dispare Disp		†		IBM_TDB	ļ		
Comparison of the content of the c	-	1	((361/283.1-283.4).CCLS.) and etch\$4 same	USPAT;	2004/04/15	10:35	1
Company	ĺ		pit same density				1
Company				1			1
Company Comp							1
(pits4 holes4 grooves4 recesss4 openingss)			_				1
Same density	-	0 1		· ·	2004/04/15	10:36	
Company							
Continue	ĺ		same density				
Comparison of the comparison							
(ints4 holes4 grooves4 recess\$4 opening\$4) US-PGPUB; Same density US-PGPUB; PPO, UPO, DERWENT; DPO, UPO, DPO, DPO, DPO, DPO, DPO, DPO, DPO, D			(/361/203 1-203 4) CCIS) and etch\$4 near3		2004/04/15	10.38	
Same density	_			· ·	2004/04/13	10.50	
- 919 ((361/283.1-283.4).CCLS.) and 73/754.ccls. US-PGPUB; EPC; JPC; DERWENT; IBM TDB USPĀT; US-PGPUB; EPC; JPC; DERWENT; IBM TDB US-PGPUB; EPC; JPC; DERWENT; IBM TDB US-PGPUB; EPC; JPC; DERWENT; IB							
Second Color			Same density	1			
or 73/718.ccls. or 73/724.ccls. Or 73/718.ccls. or 73/724.ccls. US-PGPUB; EPO; UPO; DERWENT; IBM TDB USPAT; IBM TDB USPAT; US-PGPUB; EPO; UPO; DERWENT; IBM TDB USPAT; US-PGPUB;							
or 73/718.ccls. or 73/724.ccls. Corroside	_	919	((361/283.1-283.4).CCLS.) and 73/754.ccls.	USPAT;	2004/04/15	10:48	
- 2 (((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/718.ccls. or 73/718.ccls. or 73/724.ccls.) and etch54 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) and 73/754.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) and (((361/283.1-283.4).CCLS.) and (((361/283.1-283.4).CCLS.)) and ((((361/283.1-283.4).CCLS.)) and (((((361/283.1-283.4).CCLS.)) and ((((((361/283.1-283.4).CCLS.))) and (((((((((((((((((((((((((((((((((((US-PGPUB;			
Company Comp		}		EPO; JPO;			
2 (((361/283.1-283.4).CCLS.) and T3/754.ccls. or 73/718.ccls. or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) and T3/754.ccls. or 73/718.ccls. or 73/754.ccls. or 73/754.ccls. or 73/718.ccls. or 73/754.ccls. or 73/754.							'
73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density ((361/283.1-283.4).CCLS.) and (37/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$, near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$\$, ame density ((361/283.1-283.4).CCLS.) and (37/724.ccls.) and (47/724.ccls.) an							
73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 2 (((361/283.1-283.4).CCLS.) and USPĀT; US-PGPUB; 73/724.ccls. or 73/718.ccls. or 01/73/754.ccls. or 01/73/754.ccls	-	2		1	2004/04/15	10:48	
opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) and USPĀT; TBM_TDB USPĀT; US-PGPUB; TSM_TOB USPĀT; US-PGPUB; TSM_TSM_TOB USPĀT; US-PGPUB; TSM_TOB USPĀT; US-PGPUB; TSM_TOB USPĀT; US-PGPUB; TSM_TOB USPĀT; US-PGPUB; TSM_TOB USPĀT; US-PGPUB; TSM_T				1			
density							
2 (((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT; EPO; JPO; DERWENT;				1			
73/754.ccls. or 73/718.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density - 2 (((361/283.1-283.4).CCLS.) and					2004/04/15	10.47	
73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$\$) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 2 (((361/283.1-283.4).CCLS.) and USPAT; US-PGFUB; PO; JPO; impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density - 0 (((361/283.1-283.4).CCLS.) and USPAT; US-PGFUB; PO; JPO; impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density - 0 (((361/283.1-283.4).CCLS.) and USPAT; US-PGFUB; PO; JPO; impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4] near4 density - 1694 ((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. - 1694 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density - 4 ((((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density - 4 (((((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density - 4 ((((((((((((((((((((((((((((((((((_	2		1	2004/04/13	10.47	
impurit\$4 dop\$\$) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density IBM_TDB 2004/04/15 10:48							
Groove\$4 recess\$4 hole\$4) same density							
2 (((361/283.1-283.4).CCLS.) and							
73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 0 (((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) near4 density 1694 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. 1694 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. 1695 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) near5 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 180	<u>-</u>	2	(((361/283.1-283.4).CCLS.) and		2004/04/15	10:48	
73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 DERWENT; groove\$4 recess\$4 hole\$4) same density 0 (((361/283.1-283.4).CCLS.) and 73/754.ccls. or 73/718.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near4 density 1694 ((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. 1694 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. 1695 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 percess\$4 hole\$4) same density 1805 (1004/04/15 10:48		-					
impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) and							
Groove\$4 recess\$4 hole\$4) same density					1		
73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 prove\$4 recess\$4 hole\$4) near4 density IBM TDB USPAT; or 73/718.ccls. or 73/724.ccls. or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 precess\$4 hole\$4) same density IBM TDB USPAT; or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 precess\$4 hole\$4) same density IBM TDB USPAT; or 73/718.ccls. or 73/724.ccls.) and US-PGPUB; etch\$4 near3 (pit\$4 opening\$4 groove\$4 precess\$4 hole\$4) same density IBM TDB USPAT; or 73/718.ccls. or 73/724.ccls.) or 73/754.ccls.							
73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) near4 density - 1694 (361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 5 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 6 (((361/283.1-283.4).CCLS.) and US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 73/718.ccls. or 73/724.ccls.) and US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 73/718.ccls. or 73/724.ccls.) and USPĀT; US-PGPUB; USPĀT; Or 73/718.ccls. or 73/724.ccls.) and US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 6 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB - 73/718.ccls. or 73/724.ccls.) and US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT; EPO; JPO; DERWENT;	-	0		1	2004/04/15	10:47	
impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) near4 density ((361/283.1-283.4).CCLS.) or 73/754.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB etch\$4 near3 (pit\$4 opening\$4 groove\$4 percess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) or 73/754.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM_TDB							
groove\$4 recess\$4 hole\$4) near4 density ((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls. or 73/718.ccls. or 73/724.ccls. or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (((361/283.1-283.4).CCLS.) or 73/754.ccls. or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT;			73/724.ccls.) and (etch\$4 concentration				
- 1694 ((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; Or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; Or 73/718.ccls. or 73/724.ccls.) and USPĀT; Or 73/718.ccls. or 73/724.ccls.) and USPĀT; US-PGPUB; (etch\$4 concentration impurit\$4 dop\$4) US-PGPUB; (etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;				1			
or 73/718.ccls. or 73/724.ccls. Or 73/718.ccls. or 73/724.ccls. US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; Or 73/718.ccls. or 73/724.ccls.) and US-PGPUB; etch\$4 near3 (pit\$4 opening\$4 groove\$4 EPO; JPO; recess\$4 hole\$4) same density DERWENT; IBM TDB US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; OF 73/718.ccls. or 73/754.ccls. USPAT; OF 73/718.ccls. or 73/724.ccls.) and US-PGPUB; EFO; JPO; DERWENT; IBM TDB USPAT; OF 73/718.ccls. or 73/724.ccls.) and US-PGPUB; EFO; JPO; DERWENT; DERWENT; DERWENT; DERWENT; DERWENT;		1.00			2004/04/15	10.40	
EPO; JPO; DERWENT; IBM_TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; US-PGPUB; etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; US-PGPUB; (etch\$4 concentration impurit\$4 dop\$4) US-PGPUB; (etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;	_	1694	((301/283.1-283.4).CCLS.) Or /3//34.CCLS.		2004/04/13	10:48	
DERWENT; IBM_TDB USPAT; or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 recess\$4 hole\$4) same density 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. DERWENT; IBM_TDB DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; OF 73/718.ccls. or 73/724.ccls. USPAT; or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;			OI /3//10.CCIS. OI /3//24.CCIS.				
- 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 EPO; JPO; DERWENT; IBM_TDB - 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;							
- 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 EPO; JPO; DERWENT; IBM_TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;				1			
or 73/718.ccls. or 73/724.ccls.) and etch\$4 near3 (pit\$4 opening\$4 groove\$4 EPO; JPO; recess\$4 hole\$4) same density DERWENT; IBM TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;	_	Λ	(((361/283.1-283.4).CCLS.) or 73/754.ccls.		2004/04/15	10:48	
etch\$4 near3 (pit\$4 opening\$4 groove\$4		1		1			
recess\$4 hole\$4) same density DERWENT; IBM_TDB (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPAT; or 73/718.ccls. or 73/724.ccls.) and (etch\$4 concentration impurit\$4 dop\$4) near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT; DERWENT; DERWENT; DERWENT;							
Compared to the content of the con							
- 4 (((361/283.1-283.4).CCLS.) or 73/754.ccls. USPĀT; 2004/04/15 10:49 or 73/718.ccls. or 73/724.ccls.) and US-PGPUB; (etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;							
(etch\$4 concentration impurit\$4 dop\$4) EPO; JPO; near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;	-	4	(((361/283.1-283.4).CCLS.) or 73/754.ccls.		2004/04/15	10:49	
near3 (pit\$4 opening\$4 groove\$4 recess\$4 DERWENT;			or 73/718.ccls. or 73/724.ccls.) and	US-PGPUB;			
			(etch\$4 concentration impurit\$4 dop\$4)	· ·			
hole\$4) same density IBM TDB				i i			
		1	hole\$4) same density	IBM TDB			

-	261	(diaphragm membrane elastic\$5 flexible	USPAT;	2004/04/15 10:52	٦
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;	ŀ	
		conduct\$4 same etch\$4 same (pit\$4 hole\$4	EPO; JPO;		
		groove\$4 recess\$4 opening\$4)	DERWENT;		
			IBM_TDB		
-	8	(((361/283.1-283.4).CCLS.) and	USPAT;	2004/04/15 10:52	
		73/754.ccls. or 73/718.ccls. or	US-PGPUB;		
	ļ.	73/724.ccls.) and ((diaphragm membrane	EPO; JPO;		
		elastic\$5 flexible deformable elastom\$5	DERWENT;		
		resilient\$5) near2 conduct\$4 same etch\$4	IBM_TDB		
		same (pit\$4 hole\$4 groove\$4 recess\$4			
		opening\$4))	1		
_	12	(diaphragm membrane elastic\$5 flexible	USPAT;	2004/04/15 10:53	
		deformable elastom\$5 resilient\$5) near2	US-PGPUB;		1
		conduct\$4 same etch\$4 same (pit\$4 hole\$4	EPO; JPO;		1
		groove\$4 recess\$4 opening\$4) same density	DERWENT;		
			IBM TDB		╝